SN74AHCT1G14 SINGLE SCHMITT-TRIGGER INVERTER GATE

SCLS322C - MARCH 1996 - REVISED NOVEMBER 1996

- Inputs Are TTL-Voltage Compatible
- EPIC[™] (Enhanced-Performance Implanted CMOS) Process
- Packaged in Plastic Small-Outline Transistor Package

DBV PACKAGE (TOP VIEW) NC 1 5 VCC A 2 GND 3 4 Y

description

NC - No internal connection

The SN74AHCT1G14 contains a single inverter gate. The device performs the Boolean function $Y = \overline{A}$.

The device functions as an independent inverter gate, but because of the Schmitt action, gates may have different input threshold levels for positive- (V_{T+}) and negative-going (V_{T-}) signals.

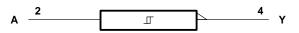
The SN74AHCT1G14 is characterized for operation from -40°C to 85°C.

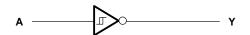
FUNCTION TABLE

INPUTS	OUTPUT
Α	Υ
Н	L
L	Н

logic symbol†

logic diagram (positive logic)







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[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} –0.5 V to 7 V Continuous output current, I_O ($V_O = 0$ to V_{CC}) ± 25 mA Continuous current through V_{CC} or GND ±50 mA Storage temperature range, T_{sto} –65°C to 150°C

recommended operating conditions (see Note 3)

		MIN	MAX	UNIT
VCC	Supply voltage	4.5	5.5	V
VIH	High-level input voltage	2.1		V
V_{IL}	Low-level input voltage		0.5	V
V_{I}	Input voltage	0	5.5	V
٧o	Output voltage	0	VCC	V
IOH	High-level output current		-8	mA
loL	Low-level output current		8	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		20	ns/V
T _A	Operating free-air temperature	-40	85	°C

NOTE 3: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	vcc	T _A = 25°C			MIN	MAX	UNIT
			MIN	TYP	MAX	IVIIIN	WAX	UNII
V _{T+}		4.5 V			3.15		3.15	V
Positive-going input threshold voltage		5.5 V			3.85		3.85	V
V _{T-}		4.5 V	1.35			1.35		V
Negative-going input threshold voltage		5.5 V	1.65			1.65		V
ΔV_{T}		4.5 V	0.4		1.4	0.4	1.4	V
Hysteresis (V _{T+} – V _{T-})		5.5 V	0.5		1.6	0.5	1.6	
Vall	$I_{OH} = -50 \mu A$	4.5 V	4.4	4.5		4.4		V
Voн	$I_{OH} = -8 \text{ mA}$	4.5 V	3.94			3.8		
V _{OL}	I _{OL} = 50 μA	4.5 V			0.1		0.1	٧
	$I_{OL} = 8 \text{ mA}$	4.5 V			0.36		0.44	
lį	$V_I = V_{CC}$ or GND	5.5 V			±0.1		±1	μΑ
Icc	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V			2		20	μΑ
C _i	V _I = V _{CC} or GND	5 V		2	10		10	pF



[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

^{2.} The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 25

PRODUCT PREVIEW

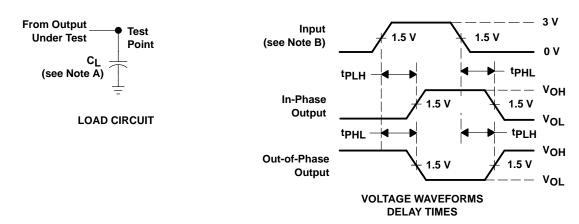
switching characteristics over recommended operating free-air temperature range V_{CC} = 5 V \pm 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM	то	LOAD CAPACITANCE	T _A = 25°C			MIN	MAX	UNIT
	(INPUT) ((OUTPUT)		MIN	TYP	MAX	l WIIN	WAX	UNII
^t PLH		V	C _I = 15 pF		4	7	1	8	no
^t PHL	A	Ť	CL = 15 pr		4	7	1	8	ns
^t PLH	_	V	C: - 50 pF		5.5	8	1	9	
t _{PHL}	A	'	C _L = 50 pF		5.5	8	1	9	ns

operating characteristics, $V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$

PARAMETER		TEST CO	NDITIONS	TYP	UNIT
C _{pd}	Power dissipation capacitance	No load,	f = 1 MHz	12	pF

PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.

- B. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, $Z_O = 50 \Omega$, $t_f = 3 \text{ ns}$, $t_f = 3 \text{ ns}$.
- C. The output is measured with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

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